

ISO7741/ISO7741-Q1/ISO7741E-Q1 Functional Safety FIT Rate, FMD and Pin FMA



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1 Overview

This document contains information for ISO7741/ISO7741-Q1/ISO7741E-Q1 (16-QSOP, 16-DW packages) and ISO7741-Q1 (16-DWW package) to aid in a functional safety system design. Information provided are:

- Functional Safety Failure In Time (FIT) rates of the semiconductor component estimated by the application of industry reliability standards
- Component failure modes and their distribution (FMD) based on the primary function of the device
- Pin failure mode analysis (Pin FMA)

Figure 1-1 shows the device functional block diagram of one channel of ISO7741/ISO7741-Q1/ISO7741E-Q1 for reference.

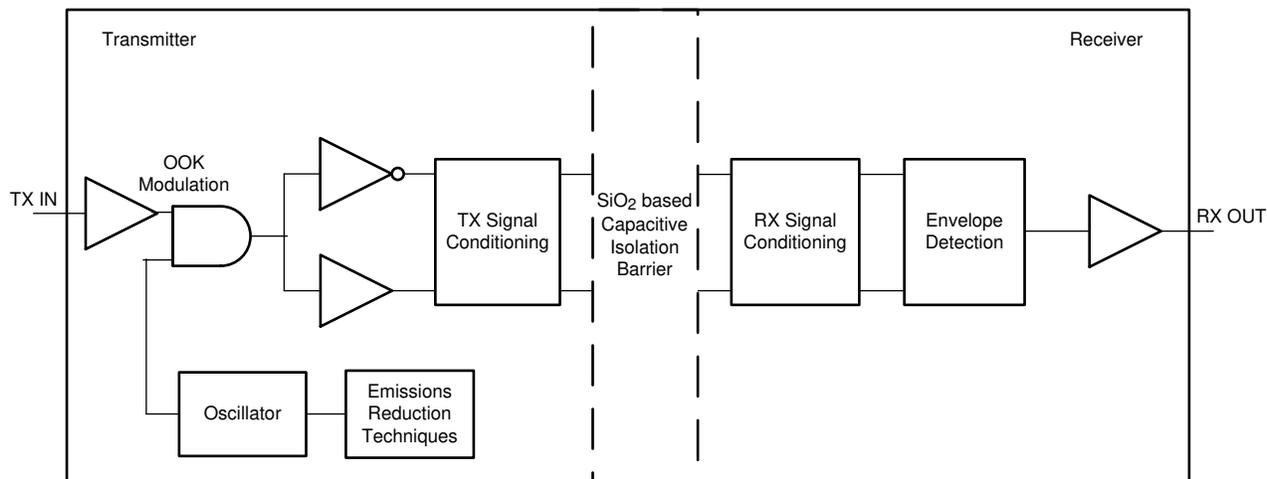


Figure 1-1. Functional Block Diagram

ISO7741/ISO7741-Q1/ISO7741E-Q1 was developed using a quality-managed development process, but was not developed in accordance with the IEC 61508 or ISO 26262 standards.

2 Functional Safety Failure In Time (FIT) Rates

2.1 16-QSOP (SSOP) Package

This section provides Functional Safety Failure In Time (FIT) rates for 16-QSOP package of ISO7741/ISO7741-Q1 based on two different industry-wide used reliability standards:

- [Table 2-1](#) provides FIT rates based on IEC TR 62380 / ISO 26262 part 11
- [Table 2-2](#) provides FIT rates based on the Siemens Norm SN 29500-2

Table 2-1. Component Failure Rates per IEC TR 62380 / ISO 26262 Part 11

FIT IEC TR 62380 / ISO 26262	FIT (Failures Per 10 ⁹ Hours)
Total Component FIT Rate	13
Die FIT Rate	4
Package FIT Rate	9

The failure rate and mission profile information in [Table 2-1](#) comes from the Reliability data handbook IEC TR 62380 / ISO 26262 part 11:

- Mission Profile: Motor Control from Table 11
- Power dissipation: 200 mW
- Climate type: World-wide Table 8
- Package factor (lambda 3): Table 17b
- Substrate Material: FR4
- EOS FIT rate assumed: 0 FIT

Table 2-2. Component Failure Rates per Siemens Norm SN 29500-2

Table	Category	Reference FIT Rate	Reference Virtual T _J
5	CMOS, BICMOS Digital, analog / mixed	25 FIT	55 °C

The Reference FIT Rate and Reference Virtual T_J (junction temperature) in [Table 2-2](#) come from the Siemens Norm SN 29500-2 tables 1 through 5. Failure rates under operating conditions are calculated from the reference failure rate and virtual junction temperature using conversion information in SN 29500-2 section 4.

2.2 16-SOIC (wide-body SOIC) Package

This section provides Functional Safety Failure In Time (FIT) rates for the 16-SOIC package of ISO7741/ISO7741-Q1/ISO7741E-Q1 based on two different industry-wide used reliability standards:

- [Table 2-3](#) provides FIT rates based on IEC TR 62380 / ISO 26262 part 11
- [Table 2-4](#) provides FIT rates based on the Siemens Norm SN 29500-2

Table 2-3. Component Failure Rates per IEC TR 62380 / ISO 26262 Part 11

FIT IEC TR 62380 / ISO 26262	FIT (Failures Per 10 ⁹ Hours)
Total Component FIT Rate	28
Die FIT Rate	3
Package FIT Rate	25

The failure rate and mission profile information in [Table 2-3](#) comes from the Reliability data handbook IEC TR 62380 / ISO 26262 part 11:

- Mission Profile: Motor Control from Table 11
- Power dissipation: 200 mW
- Climate type: World-wide Table 8
- Package factor (λ_3): Table 17b
- Substrate Material: FR4
- EOS FIT rate assumed: 0 FIT

Table 2-4. Component Failure Rates per Siemens Norm SN 29500-2

Table	Category	Reference FIT Rate	Reference Virtual T _J
5	CMOS, BICMOS Digital, analog / mixed	25 FIT	55 °C

The Reference FIT Rate and Reference Virtual T_J (junction temperature) in [Table 2-4](#) come from the Siemens Norm SN 29500-2 tables 1 through 5. Failure rates under operating conditions are calculated from the reference failure rate and virtual junction temperature using conversion information in SN 29500-2 section 4.

2.3 16-DWW (extra wide-body SOIC) Package

This section provides Functional Safety Failure In Time (FIT) rates for the 16-DWW package of ISO7741-Q1 based on two different industry-wide used reliability standards:

- [Table 2-5](#) provides FIT rates based on IEC TR 62380 / ISO 26262 part 11
- [Table 2-6](#) provides FIT rates based on the Siemens Norm SN 29500-2

Table 2-5. Component Failure Rates per IEC TR 62380 / ISO 26262 Part 11

FIT IEC TR 62380 / ISO 26262	FIT (Failures Per 10 ⁹ Hours)
Total Component FIT Rate	48
Die FIT Rate	3
Package FIT Rate	45

The failure rate and mission profile information in [Table 2-5](#) comes from the Reliability data handbook IEC TR 62380 / ISO 26262 part 11:

- Mission Profile: Motor Control from Table 11
- Power dissipation: 200 mW
- Climate type: World-wide Table 8
- Package factor (lambda 3): Table 17b
- Substrate Material: FR4
- EOS FIT rate assumed: 0 FIT

Table 2-6. Component Failure Rates per Siemens Norm SN 29500-2

Table	Category	Reference FIT Rate	Reference Virtual T _J
5	CMOS, BICMOS Digital, analog / mixed	25 FIT	55 °C

The Reference FIT Rate and Reference Virtual T_J (junction temperature) in [Table 2-6](#) come from the Siemens Norm SN 29500-2 tables 1 through 5. Failure rates under operating conditions are calculated from the reference failure rate and virtual junction temperature using conversion information in SN 29500-2 section 4.

3 Failure Mode Distribution (FMD)

The failure mode distribution estimation for ISO7741/ISO7741-Q1/ISO7741E-Q1 in [Table 3-1](#) comes from the combination of common failure modes listed in standards such as IEC 61508 and ISO 26262, the ratio of sub-circuit function size and complexity and from best engineering judgment.

The failure modes listed in this section reflect random failure events and do not include failures due to misuse or overstress.

Table 3-1. Die Failure Modes and Distribution

Die Failure Modes	Failure Mode Distribution (%)
OUT state undetermined	35%
OUT not in timing or voltage specification	30%
OUT stuck to default state	25%
OUT stuck high	5%
OUT stuck low	5%

The FMD in [Table 3-1](#) excludes short circuit faults across the isolation barrier. Faults for short circuit across the isolation barrier can be excluded according to ISO 61800-5-2:2016 if the following requirements are fulfilled:

1. The signal isolation component is OVC III according to IEC 61800-5-1. If a SELV/PELV power supply is used, pollution degree 2/OVC II applies. All requirements of IEC 61800-5-1:2007, 4.3.6 apply.
2. Measures are taken to ensure that an internal failure of the signal isolation component cannot result in excessive temperature of its insulating material.

Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance.

4 Pin Failure Mode Analysis (Pin FMA)

This section provides a Failure Mode Analysis (FMA) for the pins of the ISO7741/ISO7741-Q1/ISO7741E-Q1 (16-QSOP, 16-DW packages) and ISO7741-Q1 (16-DWW package). The failure modes covered in this document include the typical pin-by-pin failure scenarios:

- Pin short-circuited to Ground (see [Table 4-2](#))
- Pin open-circuited (see [Table 4-3](#))
- Pin short-circuited to an adjacent pin (see [Table 4-4](#))
- Pin short-circuited to supply (see [Table 4-5](#))

[Table 4-2](#) through [Table 4-5](#) also indicate how these pin conditions can affect the device as per the failure effects classification in [Table 4-1](#). Note that when pin short to ground case is discussed, only same side ground shorts are considered.

Table 4-1. TI Classification of Failure Effects

Class	Failure Effects
A	Potential device damage that affects functionality
B	No device damage, but loss of functionality
C	No device damage, but performance degradation
D	No device damage, no impact to functionality or performance

4.1 16-QSOP (SSOP), 16-DW (wide-body SOIC) and 16-DWW (extra wide-body SOIC) Package

[Figure 4-1](#) shows the ISO7741/ISO7741-Q1/ISO7741E-Q1 pin diagram for all three packages, 16-QSOP, 16-DW and 16-DWW. For a detailed description of the device pins please refer to the *Pin Configuration and Functions* section in the ISO7741/ISO7741-Q1/ISO7741E-Q1 data sheet.

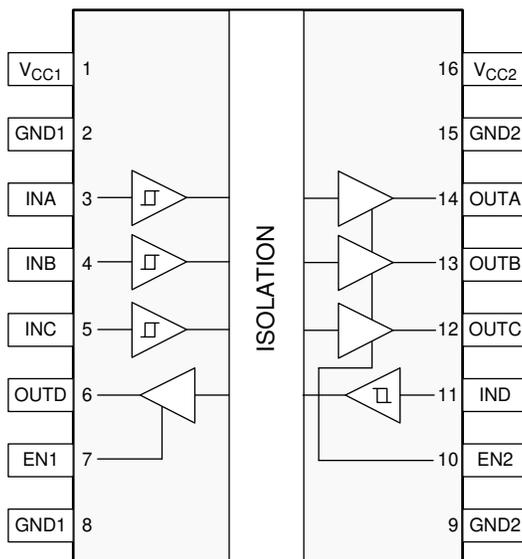


Figure 4-1. Pin Diagram (common for all 3 Packages)

Table 4-2. Pin FMA for Device Pins Short-Circuited to Ground

Pin Name	Pin No.	Description of Potential Failure Effect(s)	Failure Effect Class
V _{CC1}	1	No power to the device on side-1. Observe that the absolute maximum ratings for all pins of the device are met; otherwise device damage may be plausible. OUTD state undetermined.	A
GND1	2	Device continues to function as expected.	D
INA	3	Input signal shorted to ground, so output (OUTA) stuck to low. Communication from INA to OUTA corrupted.	B
INB	4	Input signal shorted to ground, so output (OUTB) stuck to low. Communication from INB to OUTB corrupted.	B
INC	5	Input signal shorted to ground, so output (OUTC) stuck to low. Communication from INC to OUTC corrupted.	B
OUTD	6	OUTD stuck low. Data communication from IND to OUTD lost. Device damage possible if IND is driven high for extended period of time.	A
EN1	7	Disables output buffer for OUTD. Communication corrupted for Channel D.	B
GND1	8	Device continues to function as expected. Normal operation.	D
GND2	9	Device continues to function as expected. Normal operation.	D
EN2	10	Disables the output buffer for OUTA/OUTB/OUTC channels. Communication corrupted.	B
IND	11	Input signal shorted to ground, so output (OUTD) stuck to low. Communication from IND to OUTD corrupted.	B
OUTC	12	OUTC stuck low. Data communication from INC to OUTC lost. Device damage possible if INC is driven high for extended period of time.	A
OUTB	13	OUTB stuck low. Data communication from INB to OUTB lost. Device damage possible if INB is driven high for extended period of time.	A
OUTA	14	OUTA stuck low. Data communication from INA to OUTA lost. Device damage possible if INA is driven high for extended period of time.	A
GND2	15	Device continues to function as expected. Normal operation.	D
V _{CC2}	16	No power to the device on side-2. OUTA/OUTB/OUTC pins state undetermined.	B

Table 4-3. Pin FMA for Device Pins Open-Circuited

Pin Name	Pin No.	Description of Potential Failure Effect(s)	Failure Effect Class
V _{CC1}	1	Operation undetermined. Either device is unpowered and OUTA/OUTB/OUTC=default logic state, OUTD=undetermined or through internal ESD diode on INA/INB/INC pin, device can power up if any IN is driven to logic high. If IN has current sourcing capability to provide regular operating current of device, ESD diode conducts that current and device damage plausible.	A
GND1	2	Device gets return ground through pin8. Normal operation.	D
INA	3	No communication to INA channel possible. OUTA stuck to default state (High for ISO7741/ISO7741-Q1/ISO7741E-Q1 and Low for ISO7741F/ISO7741F-Q1/ISO7741FE-Q1).	B
INB	4	No communication to INB channel possible. OUTB stuck to default state (High for ISO7741/ISO7741-Q1/ISO7741E-Q1 and Low for ISO7741F/ISO7741F-Q1/ISO7741FE-Q1).	B
INC	5	No communication to INC channel possible. OUTC stuck to default state (High for ISO7741/ISO7741-Q1/ISO7741E-Q1 and Low for ISO7741F/ISO7741F-Q1/ISO7741FE-Q1).	B
OUTD	6	State of OUTD undetermined. Data communication from IND to OUTD lost.	B
EN1	7	Control on OUTD output buffer lost, but communication from IN to OUT channels continues normally.	B
GND1	8	Device gets return ground through pin2. Normal operation.	D
GND2	9	Device gets return ground through pin15. Normal operation.	D
EN2	10	Control on OUTA/OUTB/OUTC output buffer lost, but communication from IN to OUT channels continues normally.	B
IND	11	No communication to IND channel possible. OUTD stuck to default state (High for ISO7741/ISO7741-Q1/ISO7741E-Q1 and Low for ISO7741F/ISO7741F-Q1/ISO7741FE-Q1).	B
OUTC	12	State of OUTC undetermined. Data communication from INC to OUTC lost.	B
OUTB	13	State of OUTB undetermined. Data communication from INB to OUTB lost.	B

Table 4-3. Pin FMA for Device Pins Open-Circuited (continued)

Pin Name	Pin No.	Description of Potential Failure Effect(s)	Failure Effect Class
OUTA	14	State of OUTA undetermined. Data communication from INA to OUTA lost.	B
GND2	15	Device gets return ground through pin9. Normal operation.	D
V _{CC2}	16	Device unpowered on side-2 and state of OUTA/OUTB/OUTC undetermined.	B

Table 4-4. Pin FMA for Device Pins Short-Circuited to Adjacent Pin

Pin Name	Pin No.	Shorted to	Description of Potential Failure Effect(s)	Failure Effect Class
V _{CC1}	1	GND1	No power to the device on side-1. Observe that the absolute maximum ratings for all pins of the device are met; otherwise device damage may be plausible.	A
GND1	2	INA	Input signal shorted to ground, so output (OUTA) stuck to low. Communication from INA to OUTA corrupted.	B
INA	3	INB	Communication corrupted for either INA or INB channel.	B
INB	4	INC	Communication corrupted for either INA or INB channel.	B
INC	5	OUTD	Communication corrupted for either or both channels. With opposite logic state on both channels, high current can flow between supply and ground and cause possible device damage.	A
OUTD	6	EN1	Communication corrupted on Channel D. If EN1 is pulled to supply externally, possible device damage if OUTD driven low for extended duration.	A
EN1	7	GND1	Disables OUTD output buffer. Communication for channel D corrupted.	B
GND1	8	EN1	Already considered in above row.	B
GND2	9	EN2	Disables the output buffer for all OUTA/OUTB/OUTC Output channels. Communication corrupted.	B
EN2	10	IND	Communication corrupted on Channel D if EN2 is pulled high or low externally. When IND toggles, communication corrupted on other channels whose output buffer is controlled by EN2.	B
IND	11	OUTC	Communication corrupted for either or both channels. With opposite logic state on both channels, high current can flow between supply and ground and cause possible device damage.	A
OUTC	12	OUTB	Communication corrupted for either or both channels. With opposite logic state on both channels, high current can flow between supply and ground and cause possible device damage.	A
OUTB	13	OUTA	Communication corrupted for either OUTA or OUTB channel. Device damage possible if INA and INB try to drive opposite logic state for extended duration creating a short between supply and ground on side-2.	A
OUTA	14	GND2	OUTA stuck low. Data communication from INA to OUTA lost. Device damage possible if INA is driven high for extended period of time.	A
GND2	15	V _{CC2}	No power to the device on side-2. OUTA/OUTB/OUTC pins state undetermined.	B
V _{CC2}	16	GND2	Already considered in above row.	B

Table 4-5. Pin FMA for Device Pins Short-Circuited to supply

Pin Name	Pin No.	Description of Potential Failure Effect(s)	Failure Effect Class
V _{CC1}	1	No effect. Normal operation.	D
GND1	2	This can create potential difference between pin2 and pin8, causing high current to flow in device and potential device damage.	A
INA	3	INA pin stuck high. Communication corrupted. OUTA state high.	B
INB	4	INB pin stuck high. Communication corrupted. OUTB state high.	B
INC	5	INC pin stuck high. Communication corrupted. OUTC state high.	B
OUTD	6	OUTD stuck high. Data communication from INC to OUTC lost. Device damage possible if IND is driven low for extended period of time.	A
EN1	7	Functionality to disable output buffer OUTD lost. Communication for all channels normal.	B
GND1	8	This can create potential difference between pin2 and pin8, causing high current to flow in device and potential device damage.	A
GND2	9	This can create potential difference between pin9 and pin15, causing high current to flow in device and potential device damage.	A
EN2	10	Functionality to disable output buffer for OUTA/OUTB/OUTC lost. Communication for all channels normal.	B
IND	11	IND pin stuck high. Communication corrupted. OUTD state high.	B

Table 4-5. Pin FMA for Device Pins Short-Circuited to supply (continued)

Pin Name	Pin No.	Description of Potential Failure Effect(s)	Failure Effect Class
OUTC	12	OUTC stuck high. Communication disrupted. If INC is low for extended duration, OUTC being stuck high creates a short and can damage the device.	A
OUTB	13	OUTB stuck high. Communication disrupted. If INB is low for extended duration, OUTB being stuck high creates a short and can damage the device.	A
OUTA	14	OUTA stuck high. Communication disrupted. If INA is low for extended duration, OUTA being stuck high creates a short and can damage the device.	A
GND2	15	This can create potential difference between pin9 and pin15, causing high current to flow in device and potential device damage.	A
V _{CC2}	16	Device continues to function as expected. Normal operation.	D

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